

Features

- High Speed
 - $t_{AA} = 15 \text{ ns}$
- Low Active Power
 - $I_{CC} = 150 \text{ mA}$ at 67 MHz
- Low complementary metal oxide semiconductor (CMOS) Standby Power
 - $I_{SB2} = 25 \text{ mA}$
- Operating voltages of 1.7 V to 2.2 V
- 1.5 V data retention
- Automatic power-down when deselected
- Transistor-transistor logic (TTL) compatible inputs and outputs
- Easy memory expansion with \overline{CE}_1 and CE_2 features
- Available in Pb-free 54-Pin thin small outline package (TSOP) II package

Functional Description

The CY7C1061DV18 is a high performance CMOS Static RAM (SRAM) organized as 1,048,576 words by 16 bits.

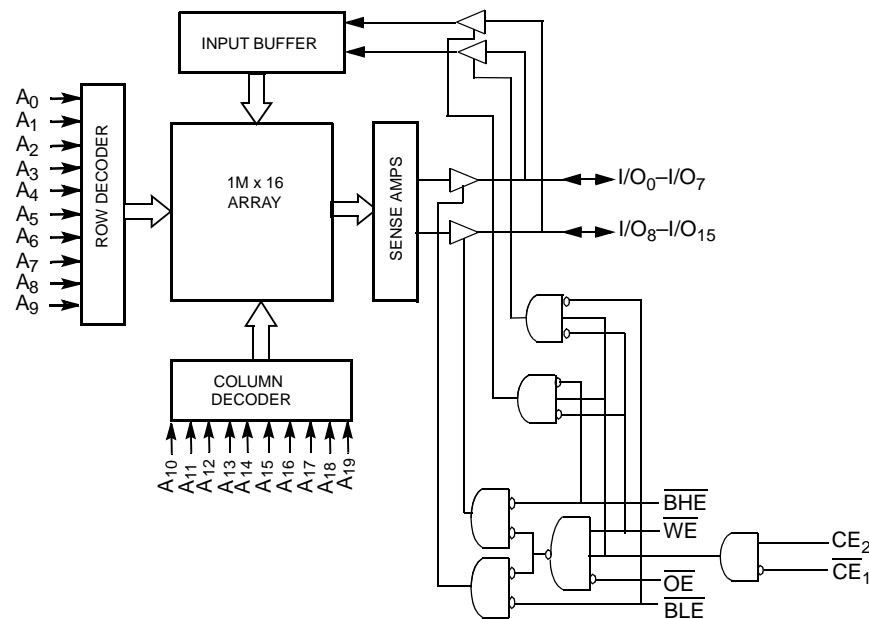
To write to the device, enable the chip (\overline{CE}_1 LOW and CE_2 HIGH) while forcing the Write Enable (WE) input LOW. If Byte Low Enable (\overline{BLE}) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{19}). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{19}).

To read from the device, enable the chip by taking \overline{CE}_1 LOW and CE_2 HIGH while forcing the Output Enable (\overline{OE}) LOW and the Write Enable (WE) HIGH. If Byte Low Enable (\overline{BLE}) is LOW, then data from the memory location specified by the address pins appears on I/O_0 to I/O_7 . If Byte High Enable (BHE) is LOW, then data from memory appears on I/O_8 to I/O_{15} . See the [Truth Table on page 9](#) for a complete description of Read and Write modes.

The input/output pins (I/O_0 through I/O_{15}) are placed in a high impedance state when the device is deselected (\overline{CE}_1 HIGH/ CE_2 LOW), the outputs are disabled (\overline{OE} HIGH), the BHE and \overline{BLE} are disabled (BHE, \overline{BLE} HIGH), or during a Write operation (\overline{CE}_1 LOW, CE_2 HIGH, and WE LOW).

The CY7C1061DV18 is available in a 54-pin TSOP II package with center power and ground (revolutionary) pinout.

Logic Block Diagram



Contents

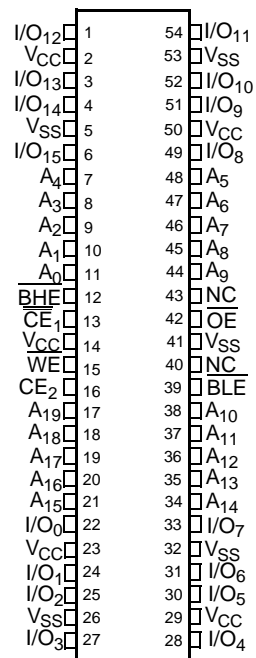
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Selection Guide

Description	-15	Unit
Maximum access time	15	ns
Maximum operating current	150	mA
Maximum CMOS standby current	25	mA

Pin Configurations

Figure 1. 54-Pin TSOP II (Top View)



Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature -65 °C to +15 °C

Ambient temperature with power applied -55 °C to +125 °C

Supply voltage on V_{CC} to relative GND^[1]...-0.2 V to +2.45 V

DC voltage applied to outputs in High Z state^[1]-0.2 V to +2.45 V

DC input voltage^[1]-0.2 V to +2.45 V

Current into outputs (LOW) 20 mA

Static discharge voltage.....>2001 V (per MIL-STD-883, method 3015)

Latch-up current >200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Industrial	-40 °C to +85 °C	1.7 V to 2.2 V

DC Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	-15		Unit
			Min	Max	
V _{OH}	Output HIGH voltage	Min V _{CC} , I _{OH} = -0.1 mA	1.4	-	V
V _{OL}	Output LOW voltage	Min V _{CC} , I _{OL} = 0.1 mA	-	0.2	V
V _{IH}	Input HIGH voltage		1.4	V _{CC} + 0.2	V
V _{IL}	Input LOW voltage ^[1]		-0.2	0.4	V
I _{IX}	Input leakage current	GND ≤ V _{IN} ≤ V _{CC}	-1	+1	μA
I _{OZ}	Output leakage current	GND ≤ V _{OUT} ≤ V _{CC} , output disabled	-1	+1	μA
I _{CC}	V _{CC} operating supply current	Max V _{CC} , f = f _{MAX} = 1/t _{RC} , I _{OUT} = 0 mA CMOS levels	-	150	mA
I _{SB1}	Automatic CE power-down current – TTL inputs	CE ₁ ≥ V _{IH} , CE ₂ ≤ V _{IL} , Max V _{CC} , V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}	-	30	mA
I _{SB2}	Automatic CE power-down current – CMOS inputs	CE ₁ ≥ V _{CC} - 0.2 V, CE ₂ ≤ 0.2 V, Max V _{CC} , V _{IN} ≥ V _{CC} - 0.2 V, or V _{IN} ≤ 0.2 V, f = 0	-	25	mA

Capacitance^[2]

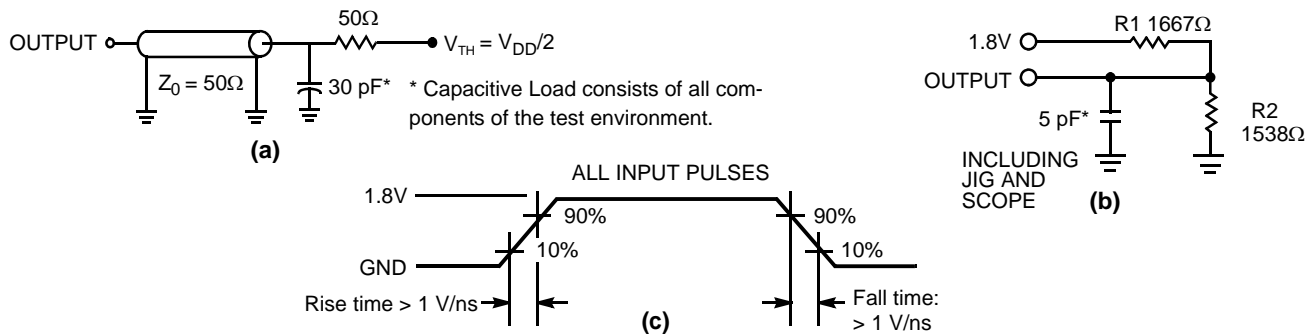
Parameter	Description	Test Conditions	TSOP II	Unit
C _{IN}	Input capacitance	T _A = 25 °C, f = 1 MHz, V _{CC} = 1.8 V.	6	pF
C _{OUT}	I/O capacitance		8	pF

Thermal Resistance

Parameter ^[2]	Description	Test Conditions	TSOP II	Unit
θ _{JA}	Thermal resistance (Junction to ambient)	Still Air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	24.18	°C/W
θ _{JC}	Thermal resistance (Junction to case)		5.40	°C/W

Notes

- V_{IL} (min) = -2.0 V for pulse durations of less than 20 ns.
- Tested initially and after any design or process changes that may affect these parameters.

Figure 2. AC Test Loads and Waveforms^[3]

AC Switching Characteristics Over the Operating Range^[4]

Parameter	Description	-15		Unit
		Min	Max	
Read Cycle				
t_{power}	$V_{CC}(\text{typical})$ to the first access ^[5]	150	–	μs
t_{RC}	Read cycle time	15	–	ns
t_{AA}	Address to data valid	–	15	ns
t_{OHA}	Data hold from address change	3	–	ns
t_{ACE}	\overline{CE}_1 LOW/ CE_2 HIGH to data valid	–	15	ns
t_{DOE}	\overline{OE} LOW to data valid	–	7	ns
t_{LZOE}	\overline{OE} LOW to Low Z	1	–	ns
t_{HZOE}	\overline{OE} HIGH to High Z ^[6]	–	7	ns
t_{LZCE}	\overline{CE}_1 LOW/ CE_2 HIGH to Low-Z ^[6]	3	–	ns
t_{HZCE}	\overline{CE}_1 HIGH/ CE_2 LOW to High-Z ^[6]	–	7	ns
t_{PU}	\overline{CE}_1 LOW/ CE_2 HIGH to Power-up ^[7]	0	–	ns
t_{PD}	\overline{CE}_1 HIGH/ CE_2 LOW to Power-down ^[7]	–	15	ns
t_{DBE}	Byte Enable to data valid	–	7	ns
t_{LZBE}	Byte Enable to Low Z	1	–	ns
t_{HZBE}	Byte Disable to High Z	–	7	ns
Write Cycle^[8, 9]				
t_{WC}	Write cycle time	15	–	ns
t_{SCE}	\overline{CE}_1 LOW/ CE_2 HIGH to write end	10	–	ns
t_{AW}	Address setup to write end	10	–	ns
t_{HA}	Address hold from write end	0	–	ns

Notes

- Valid SRAM operation does not occur until the power supplies have reached the minimum operating V_{DD} (1.5 V). 150 μs (t_{power}) after reaching the minimum operating V_{DD} , normal SRAM operation can begin including reduction in V_{DD} to the data retention (V_{CCDR} , 1.5 V) voltage.
- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 0.9 V, input pulse levels of 0 to 1.8 V. Test conditions for the Read cycle use output loading shown in part a) of the Figure 2, unless specified otherwise.
- t_{POWER} gives the minimum amount of time that the power supply should be at typical V_{CC} values until the first memory access can be performed.
- t_{HZOE} , t_{HZCE} , t_{HZWE} , t_{HZBE} , and t_{LZOE} , t_{LZCE} , t_{LZWE} , t_{LZBE} are specified with a load capacitance of 5 pF as in (b) of Figure 2. Transition is measured $\pm 200 \text{ mV}$ from steady-state voltage.
- These parameters are guaranteed by design and are not tested.
- The internal Write time of the memory is defined by the overlap of \overline{CE}_1 LOW (CE_2 HIGH) and \overline{WE} LOW. Chip enables must be active and \overline{WE} and byte enables must be LOW to initiate a Write, and the transition of any of these signals can terminate the Write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the Write.
- The minimum Write cycle time for Write Cycle No. 3 (\overline{WE} controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{SD} .

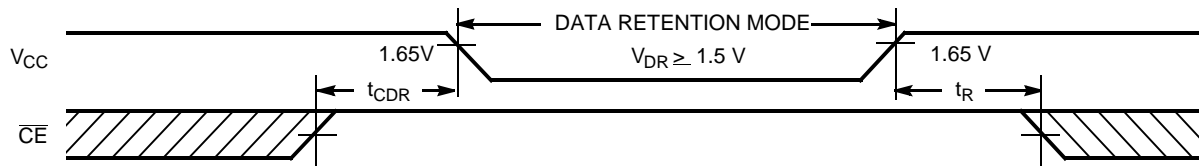
AC Switching Characteristics Over the Operating Range^[4](continued)

Parameter	Description	-15		Unit
		Min	Max	
t _{SA}	Address setup to write start	0	–	ns
t _{PWE}	\overline{WE} pulse width	10	–	ns
t _{SD}	Data setup to write end	7	–	ns
t _{HD}	Data hold from write end	0	–	ns
t _{LZWE}	\overline{WE} HIGH to Low Z ^[10]	3	–	ns
t _{HZWE}	\overline{WE} LOW to High Z ^[10]	–	7	ns
t _{BW}	Byte enable to end of write	10	–	ns

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min	Typ ^[11]	Max	Unit
V _{DR}	V _{CC} for data retention		1.5	–	–	V
I _{CCDR}	Data retention current	V _{CC} = 1.5 V, CE ₁ ≥ V _{CC} - 0.2 V, CE ₂ ≤ 0.2 V, V _{IN} ≥ V _{CC} - 0.2 V, or V _{IN} ≤ 0.2 V	–	–	25	mA
t _{CDR} ^[12]	Chip deselect to data retention time		0	–	–	ns
t _R ^[13]	Operation recovery time		t _{RC}	–	–	ns

Figure 3. Data Retention Waveform



Notes

- 10. t_{HZOE}, t_{HZCE}, t_{HZWE}, t_{HZBE}, and t_{LZOE}, t_{LZCE}, t_{LZWE}, t_{LZBE} are specified with a load capacitance of 5 pF as in (b) of Figure 2. Transition is measured ±200 mV from steady-state voltage
- 11. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC} (typ), TA = 25 °C.
- 12. Tested initially and after any design or process changes that may affect these parameters
- 13. Full device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min)} ≥ 100 μs or stable at V_{CC(min)} ≥ 100 μs.

Switching Waveforms

Figure 4. Read Cycle No. 1^[14,15]

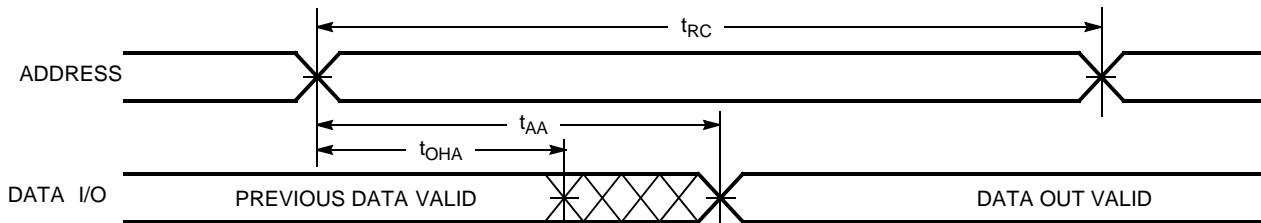
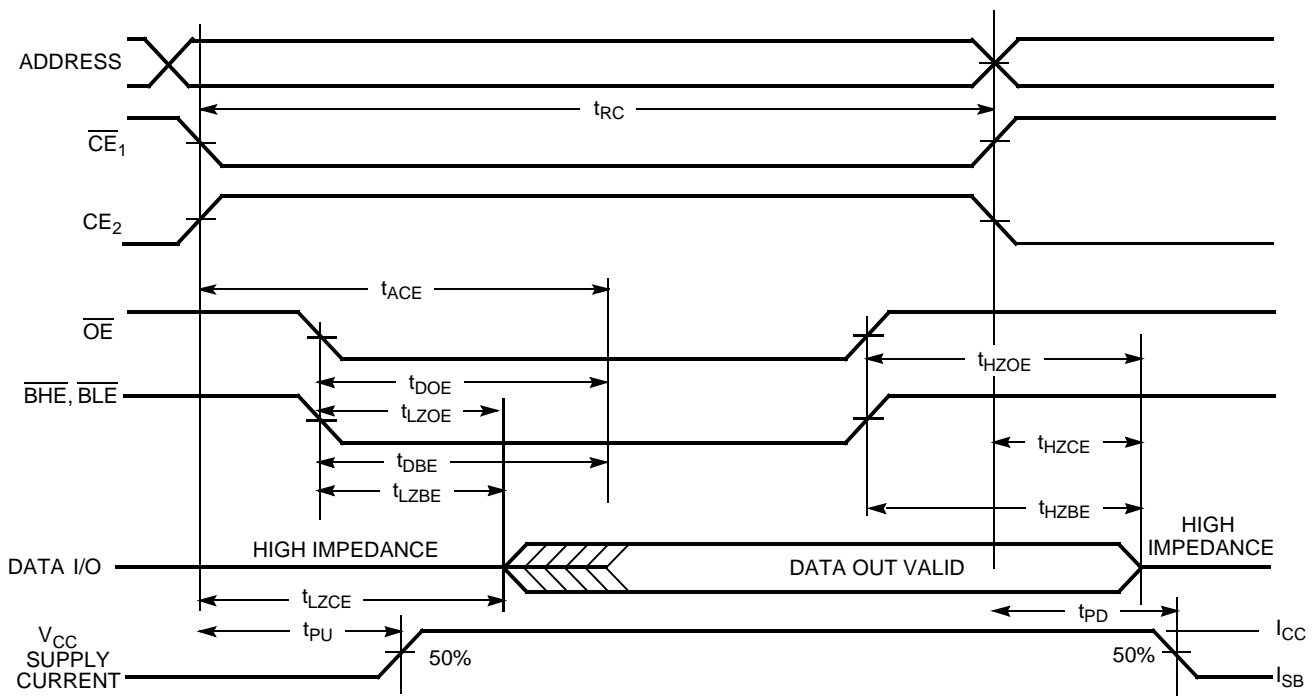


Figure 5. Read Cycle No. 2 (\overline{OE} Controlled)^[16,17]



Notes

- 14. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)}$ $\geq 100 \mu s$ or stable at $V_{CC(min)}$ $\geq 100 \mu s$.
- 15. Device is continuously selected. \overline{OE} , CE , BHE and/or BHE = V_{IL} . $CE_2 = V_{IH}$.
- 16. WE is HIGH for Read cycle.
- 17. Address valid prior to or coincident with \overline{CE}_1 transition LOW and CE_2 transition HIGH.

Figure 6. Write Cycle No. 1 (\overline{CE} Controlled)^[18,19,20]

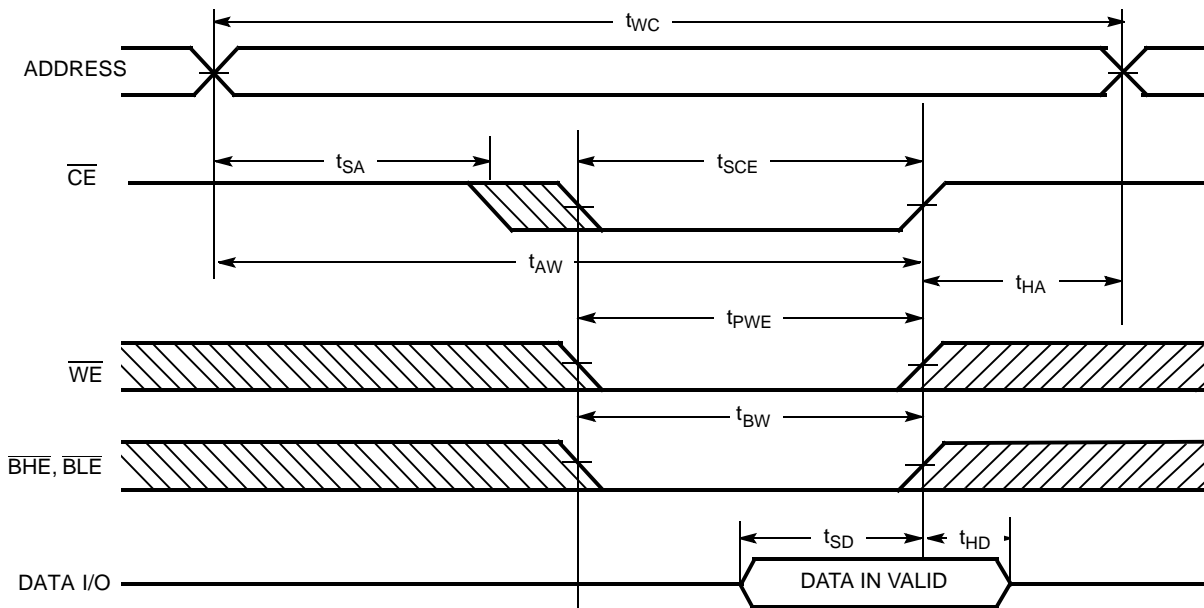
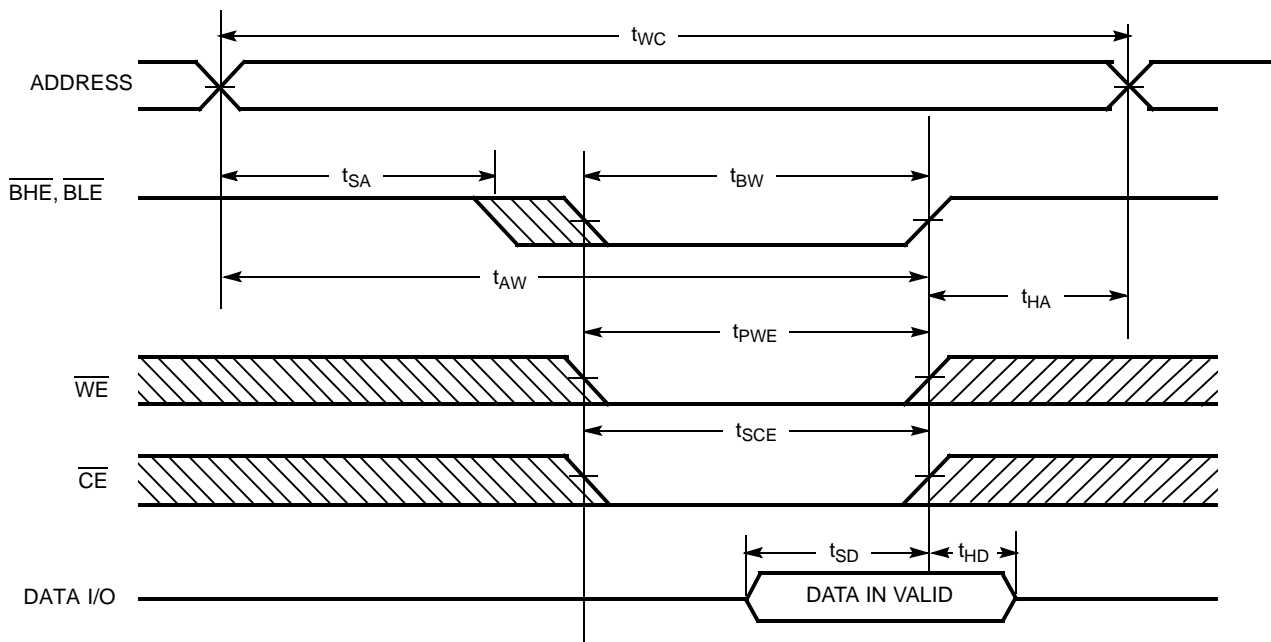


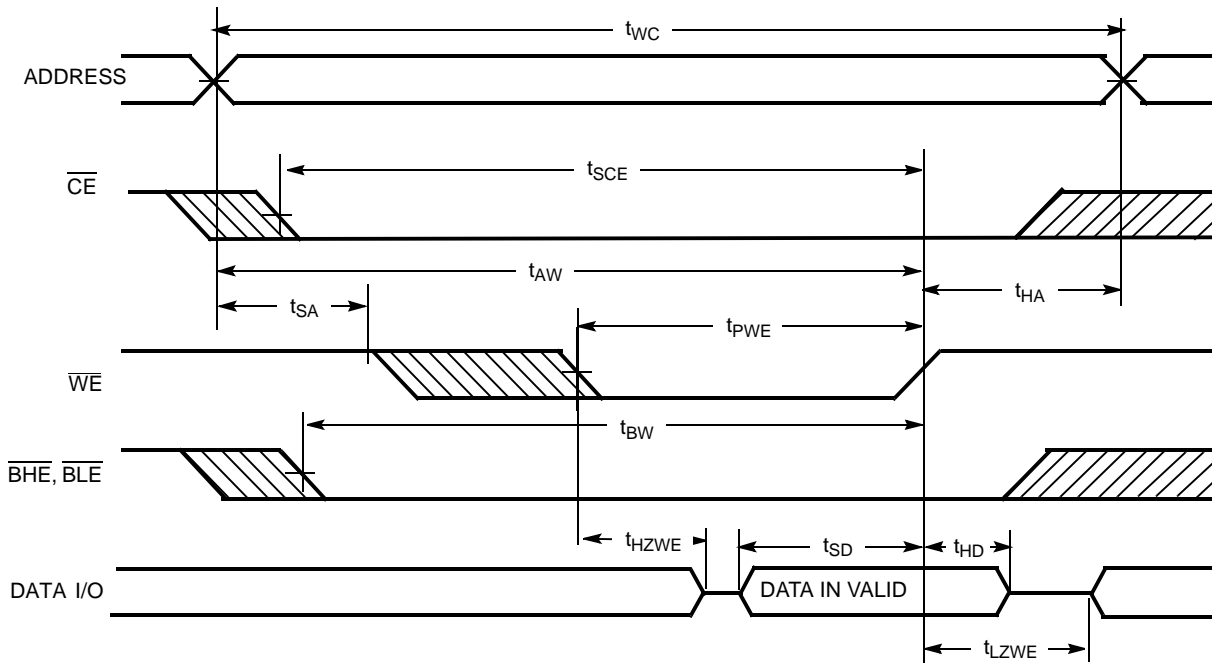
Figure 7. Write Cycle No. 2 (\overline{BLE} or \overline{BHE} Controlled)



Notes

- 18. Data I/O is high impedance if \overline{OE} or \overline{BHE} and/or $\overline{BLE} = V_{IH}$.
- 19. If CE_1 goes HIGH simultaneously with WE going HIGH, the output remains in a high impedance state.
- 20. CE is the logical combination of CE1 and CE2. When CE1 is LOW and CE2 is HIGH, CE is LOW; when CE1 is HIGH or CE2 is LOW, CE is HIGH

Figure 8. Write Cycle No. 3 (WE Controlled, OE Low)^[21,22,23]



Truth Table

\overline{CE}_1	CE_2	\overline{OE}	\overline{WE}	\overline{BLE}	\overline{BHE}	$I/O_0-I/O_7$	$I/O_8-I/O_{15}$	Mode	Power
H	X	X	X	X	X	High Z	High Z	Power-down	Standby (I_{SB})
X	L	X	X	X	X	High Z	High Z	Power-down	Standby (I_{SB})
L	H	L	H	L	L	Data out	Data out	Read all bits	Active (I_{CC})
L	H	L	H	L	H	Data out	High Z	Read lower bits only	Active (I_{CC})
L	H	L	H	H	L	High -Z	Data out	Read upper bits only	Active (I_{CC})
L	H	X	L	L	L	Data in	Data in	Write all bits	Active (I_{CC})
L	H	X	L	L	H	Data in	High Z	Write lower bits only	Active (I_{CC})
L	H	X	L	H	L	High Z	Data in	Write upper bits only	Active (I_{CC})
L	H	H	H	X	X	High Z	High Z	Selected, outputs disabled	Active (I_{CC})

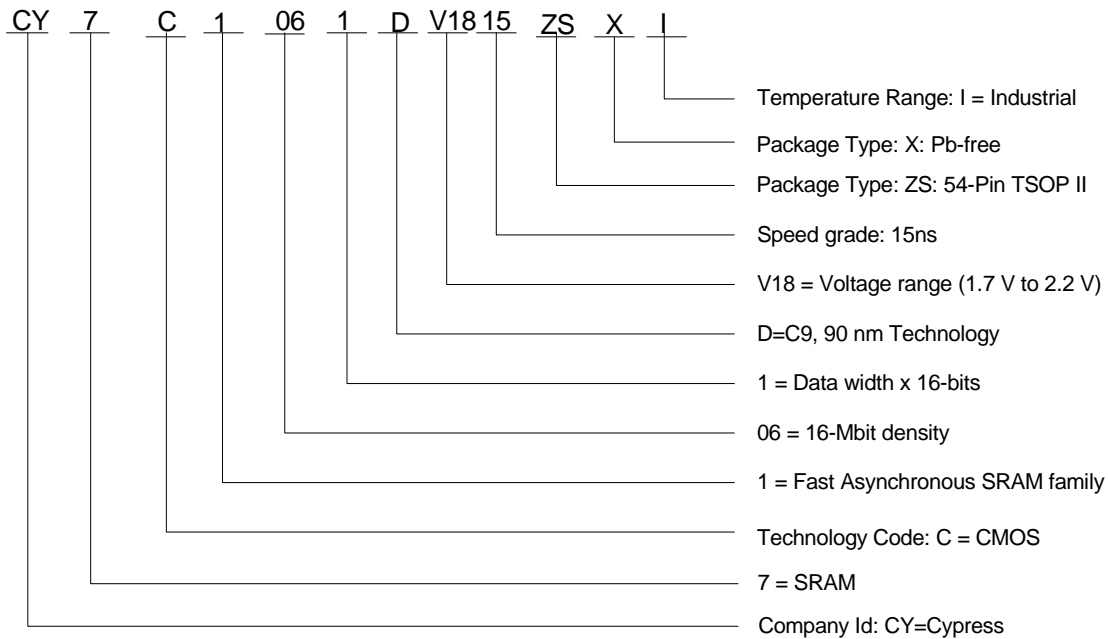
Notes

- 21. Data I/O is high impedance if \overline{OE} or \overline{BHE} and/or $\overline{BLE} = V_{IH}$.
- 22. If \overline{CE}_1 goes HIGH simultaneously with \overline{WE} going HIGH, the output remains in a high impedance state.
- 23. CE is a shorthand combination of both CE_1 and CE_2 combined. It is active LOW.

Ordering Information

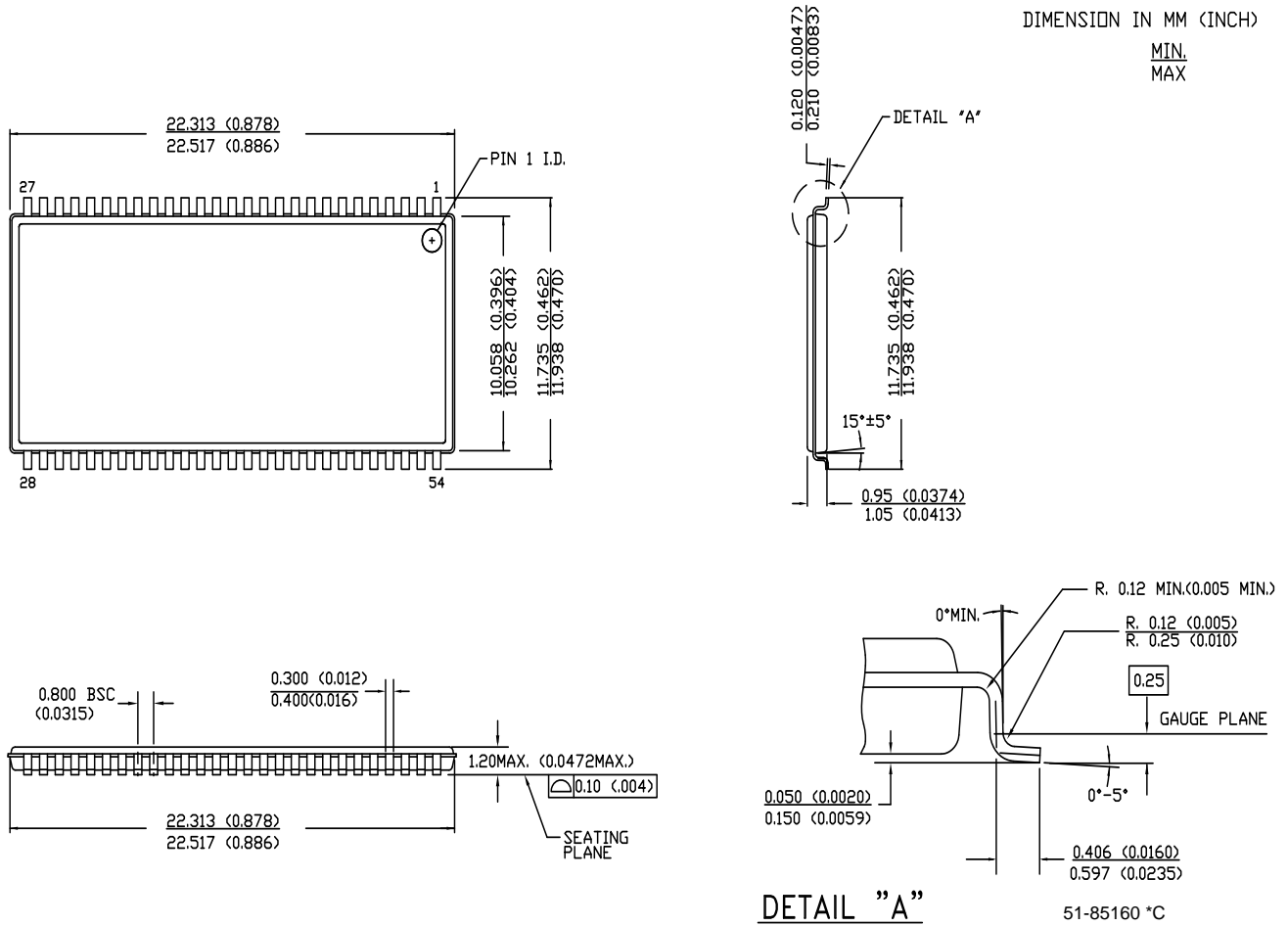
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
15	CY7C1061DV18-15ZSXI	51-85160	54 pin TSOP II (Pb-free)	Industrial

Ordering Code Definitions



Package Diagram

Figure 9. 54-pin TSOP Type II



Acronyms

Acronym	Description
CMOS	complementary metal oxide semiconductor
I/O	input/output
SRAM	static random access memory
TSOP	thin small outline package
TTL	Transistor-transistor logic

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degrees Celsius
μA	microamperes
mA	milliamperes
MHz	megahertz
ns	nanoseconds
pF	picofarads
V	volts
Ω	ohms
W	watts

Document History Page

Document Title: CY7C1061DV18 16-Mbit (1 M x 16) Static RAM				
Document Number: 001-08350				
REV.	ECN NO.	Submission Date	Orig. of Change	Description of Change
**	469420	See ECN	NXR	New data sheet
*A	2761557	09/09/2009	VKN	Updated package code
*B	2800121	11/06/2009	VKN	Increased I _{CC} limit from 100mA to 150mA Changed V _{DR} from 1.2V to 1.5V Included Thermal specs Changed t _{LZOE} and t _{LZBE} from 0ns to 1ns Changed t _{LZCE} from 0ns to 3ns Replaced 6 x 8 x 1mm FBGA package with 8 x 9.5 x 1mm FBGA package Changed status from Final to Preliminary
*C	2915361	04/16/2010	VKN	Converted from Preliminary to Final Removed 48-Ball FBGA package from the data sheet Updated links in Sales, Solutions, and Legal Information
*D	2923463	04/27/2010	RAME	Post to external web
*E	3109102	12/13/2010	PRAS	Added Ordering Code Definitions .
*F	3147322	01/19/2011	PRAS	Updated all tables notes as per template Added Acronyms and Units of Measure table.
*G	3387026	09/29/2011	TAVA	Minor technical edits. Updated Package Diagram .

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